

## isc N-Channel MOSFET Transistor

# IXTQ220N055T

#### • FEATURES

- · Drain Source Voltage-
  - : V<sub>DSS</sub>= 55V(Min)
- · Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 4m \Omega (Max)$
- · Fast Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



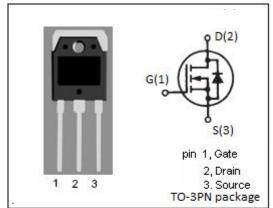
- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- · AC and DC Motor Drives
- · Robotics and Servo Controls

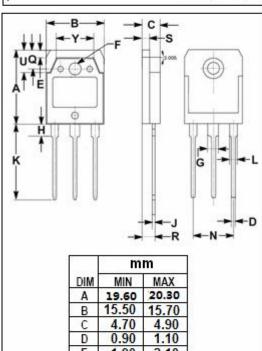
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	55	V
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±20	٧
I <sub>D</sub>	Drain Current-Continuous	220	Α
I <sub>DM</sub>	Drain Current-Single Plused	600	Α
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25°C	430	W
Tj	Max. Operating Junction Temperature	-55~175	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~175	$^{\circ}$

#### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	AX UNIT	
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.35	°C/W	





DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Υ	9.90	10.10



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#### • ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT	
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =250μA	55			V	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =4mA	2		4	V	
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 25A			4	mΩ	
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±200	nA	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =55V; V <sub>GS</sub> = 0 V <sub>DS</sub> =55V; V <sub>GS</sub> = 0;T <sub>J</sub> =175°C			5 250	μΑ	
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>F</sub> = 25A;V <sub>GS</sub> = 0			1	V	

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